



# SSC8L312PN6

## N-Channel Enhanced MOSFET

### ➤ Features

VDS	VGS	RDSON Typ.	ID
30V	±20V	0.95mΩ@10V	200A
		1.55mΩ@4V5	

### ➤ Description

This device is N-Channel enhancement MOSFET. Uses SGT technology and design to provide excellent RDSON with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. 100% UIS Tested.

### ➤ Applications

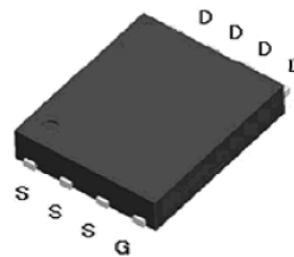
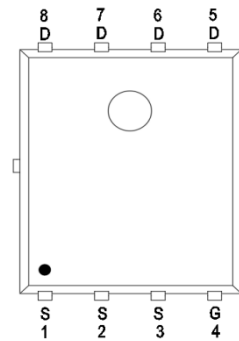
- Load Switch
- Portable Devices
- DCDC conversion
- Power supplies
- Synchronous rectification

### ➤ Ordering Information

Device	Package	Shipping
SSC8L312PN6	PDFN5X6	5000/Reel

### ➤ Pin configuration

Top view



PDFN5X6



Marking

(XX: product year / YY: product week)



➤ **Absolute Maximum Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
$V_{DSS}$	Drain-to-Source Voltage	30	V	
$V_{GSS}$	Gate-to-Source Voltage	$\pm 20$	V	
$I_D$	Continuous Drain Current <sup>d</sup>	$T_C=25^{\circ}\text{C}$	200	A
		$T_C=100^{\circ}\text{C}$	99	
$I_{DSM}$	Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}\text{C}$	60	A
		$T_A=70^{\circ}\text{C}$	41	
$I_{DM}$	Pulsed Drain Current <sup>b</sup>	400	A	
$P_D$	Power Dissipation <sup>c</sup>	$T_C=25^{\circ}\text{C}$	84	W
		$T_C=100^{\circ}\text{C}$	33	
$P_{DSM}$	Power Dissipation <sup>a</sup>	$T_A=25^{\circ}\text{C}$	7.5	W
		$T_A=70^{\circ}\text{C}$	4.8	
$I_{AS}$	Avalanche Current <sup>b</sup> L=0.1mH Single Pulse	54	A	
$E_{AS}$	Avalanche Energy <sup>b</sup> L=0.1mH Single Pulse	146	mJ	
$T_J$	Operation junction temperature	-55~150	$^{\circ}\text{C}$	
$T_{STG}$	Storage temperature range	-55~150		

➤ **Thermal Resistance Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance <sup>a</sup>	15	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	1.35	

Note:

- The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ .The value in any given application depends on the user is specific board design. The power dissipation is based on the  $t \leq 10\text{s}$  thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation  $P_D$  is based on  $T_{J(\text{MAX})}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The maximum current rating is package limited.

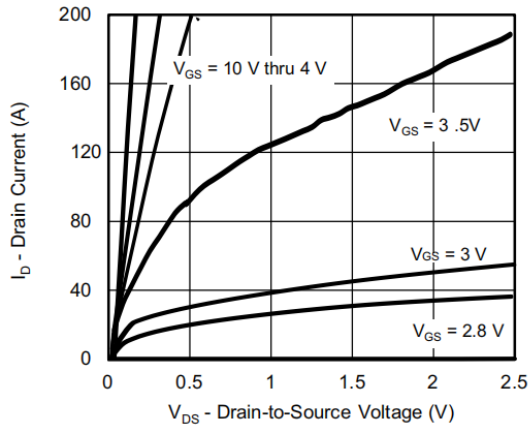


➤ **Electronics Characteristics**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

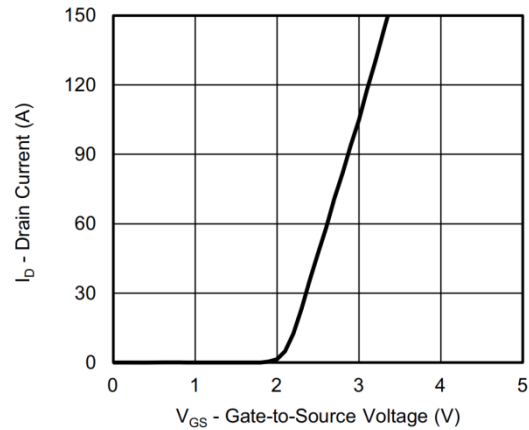
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.3	1.8	2.3	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=30A$		0.95	1.15	m $\Omega$
		$V_{GS}=4.5V, I_D=20A$		1.55	1.9	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$			1	$\mu A$
$I_{GSS}$	Gate-Source leak current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
$G_{FS}$	Transconductance	$V_{DS}=5V, I_D=20A$		100		S
$V_{SD}$	Forward Voltage	$V_{GS}=0V, I_S=20A$		0.8	1.3	V
$R_g$	Gate Resistance	$V_{DS}=0V, f=1MHz$		1.3		$\Omega$
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$		5850		pF
$C_{oss}$	Output Capacitance			3147		
$C_{rss}$	Reverse Capacitance			196		
$T_{D(ON)}$	Turn-on delay time	$V_{GS}=4.5V, R_L=1\Omega, V_{DS}=20V, R_G=3\Omega$		45		ns
$T_r$	Rise time			83		
$T_{D(OFF)}$	Turn-off delay time			56		
$T_f$	Fall time			34		
$Q_G$	Total Gate Charge	$V_{GS}=4.5V, V_{DS}=15V, I_D=30A$		44		nC
$Q_{GS}$	Gate Source Charge			28		
$Q_{GD}$	Gate Drain Charge			9.5		
$T_{rr}$	Diode Recovery Time	$I_F=30A, di/dt=100A/\mu s$		62		ns
$Q_{rr}$	Diode Recovery Charge	$I_F=30A, di/dt=100A/\mu s$		99		nC



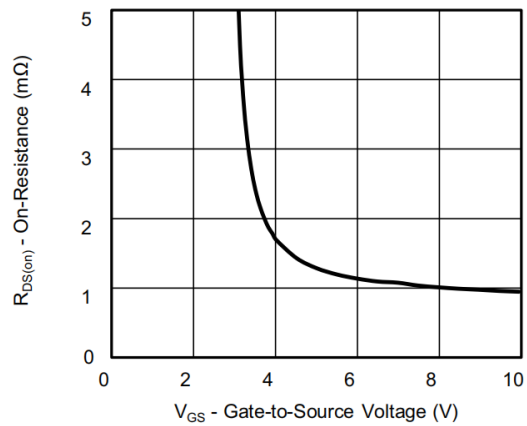
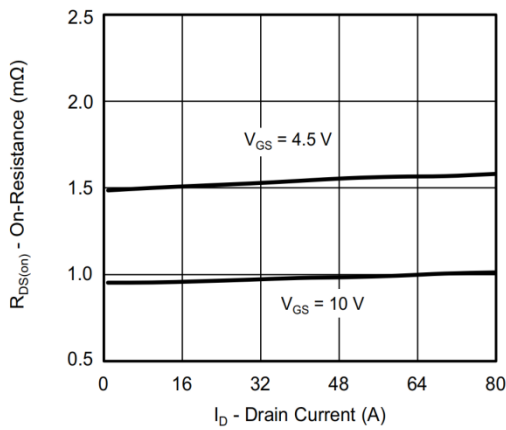
Typical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)



Output Characteristics

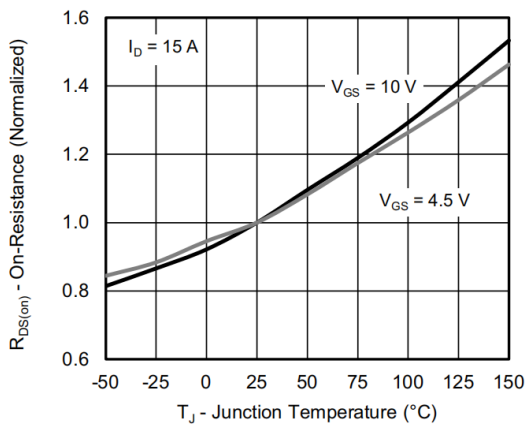


Transfer Characteristics

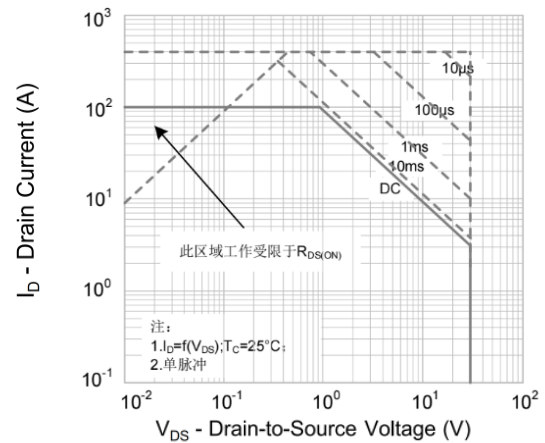


On-Resistance vs. Drain Current and Gate Voltage

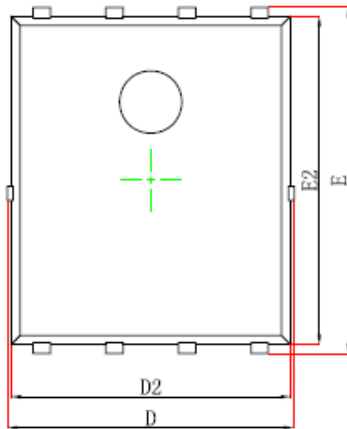
On-Resistance vs. Gate-to-Source Voltage



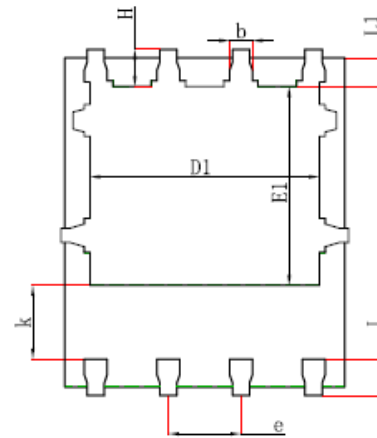
On-Resistance vs. Junction Temperature



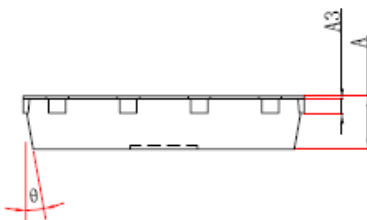
Safe Operating Area, Junction-to-Ambient

**➤ Package Information**


Top View  
[顶视图]



Bottom View  
[背视图]



Side View  
[侧视图]

Package: PDNF5X6-8L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF		0.010REF	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°



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